BUK7J1R4-40H

N-channel 40 V, 1.4 mΩ standard level MOSFET in LFPAK56E

14 September 2017 **Product data sheet**

1. General description

Automotive qualified N-channel MOSFET using the latest Trench 9 low ohmic superjunction technology, housed in an enhanced LFPAK56E package. This product has been fully designed and qualified to meet AEC-Q101 requirements delivering high performance and endurance.

2. Features and benefits

- Fully automotive qualified to AEC-Q101:
  - 175 °C rating suitable for thermally demanding environments
- Trench 9 Superjunction technology:
  - Reduced cell pitch enables enhanced power density and efficiency with lower R_{DSon} in same footprint
  - Improved SOA and avalanche capability compared to standard TrenchMOS
  - Tight $V_{GS(th)}$ limits enable easy paralleling of MOSFETs
- LFPAK Gull Wing leads:
  - High Board Level Reliability absorbing mechanical stress during thermal cycling, unlike traditional QFN packages
  - Visual (AOI) soldering inspection, no need for expensive x-ray equipment
  - Easy solder wetting for good mechanical solder joint
- LFPAK copper clip technology:
  - Improved reliability, with reduced R_{th} and R_{DSon}
  - Increases maximum current capability and improved current spreading

3. Applications

- 12 V automotive systems
- Motors, lamps and solenoid control
- Start-Stop micro-hybrid applications
- Transmission control
- Ultra high performance power switching

nexperia

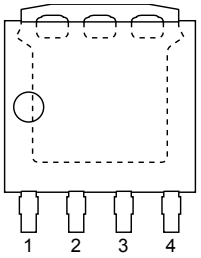
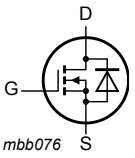
4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
V_{DS}	drain-source voltage	25 °C ≤ T_j ≤ 175 °C		-	-	40	V
I_D	drain current	V_{GS} = 10 V; T_{mb} = 25 °C		-	-	120	A
P_{tot}	total power dissipation	T_{mb} = 25 °C; Fig. 1		-	-	395	W
Static characteristics							
R_{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I_D = 25 A; T_j = 25 °C; Fig. 10		0.74	1.06	1.4	mΩ
Dynamic characteristics							
Q_{GD}	gate-drain charge	I_D = 25 A; V_{DS} = 32 V; V_{GS} = 10 V; Fig. 12; Fig. 13		-	13	34	nC
Source-drain diode							
Q_r	recovered charge	I_S = 25 A; dI_S/dt = -100 A/µs; V_{GS} = 0 V; V_{DS} = 20 V		-	39	-	nC
S	softness factor	I_S = 25 A; dI_S/dt = -100 A/µs; V_{GS} = 0 V; V_{DS} = 20 V; T_j = 25 °C; Fig. 16		-	0.7	-	

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source	 **LFPAK56E; Power-SO8 (SOT1023)**	
2	S	source		
3	S	source		
4	G	gate		
mb	D	mounting base; connected to drain		

6. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BUK7J1R4-40H	LFPAK56E; Power-SO8	plastic, single-ended surface-mounted package (LFPAK56); 4 leads; 1.27 mm pitch; 4.58 mm x 5.13 mm x 1.03 mm body	SOT1023

7. Marking

Table 4. Marking codes

Type number	Marking code
BUK7J1R4-40H	71H440

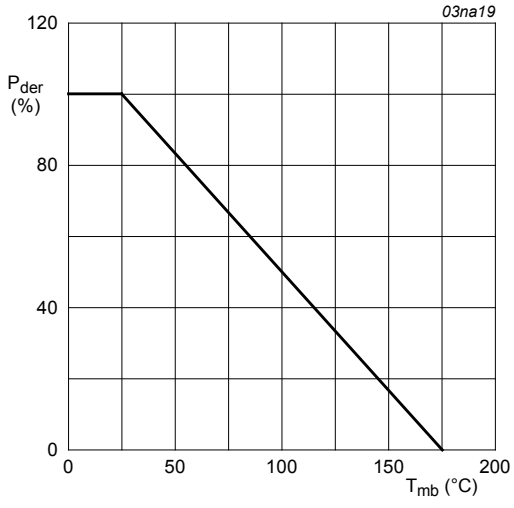
8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

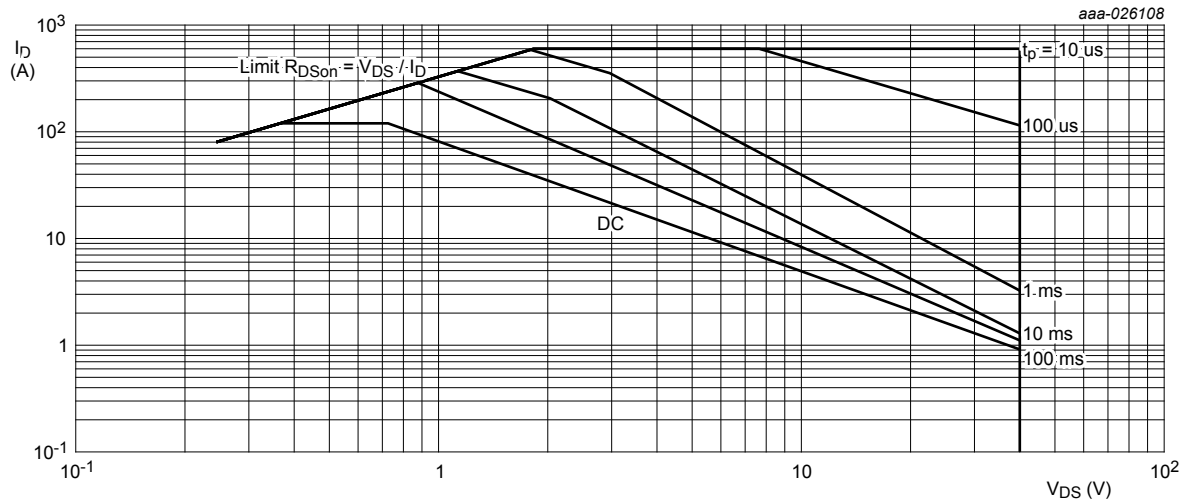
Symbol	Parameter	Conditions		Min	Max	Unit
V_{DS}	drain-source voltage	25 °C ≤ T_j ≤ 175 °C		-	40	V
V_{GS}	gate-source voltage	DC; T_j ≤ 175 °C		-10	20	V
P_{tot}	total power dissipation	T_{mb} = 25 °C; Fig. 1		-	395	W
I_D	drain current	V_{GS} = 10 V; T_{mb} = 25 °C		-	120	A
I_{DM}	peak drain current	pulsed; t_p ≤ 10 µs; T_{mb} = 25 °C; Fig. 2		-	600	A
T_{stg}	storage temperature			-55	175	°C
T_j	junction temperature			-55	175	°C
Source-drain diode						
I_S	source current	T_{mb} = 25 °C	[1]	-	120	A
I_{SM}	peak source current	pulsed; t_p ≤ 10 µs; T_{mb} = 25 °C		-	600	A
Avalanche ruggedness						
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	I_D = 120 A; V_{sup} ≤ 40 V; R_{GS} = 50 Ω; V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; unclamped; Fig. 3	[2] [3]	-	253	mJ

[1] 120A continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature.
[2] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C.
[3] Refer to application note AN10273 for further information.



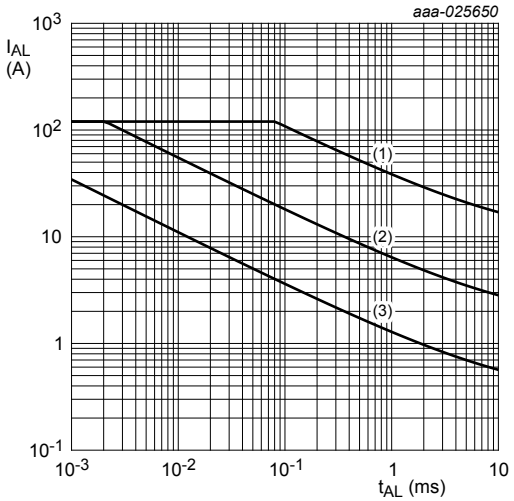
$$P_{der} = \frac{P_{tot}}{P_{tot(25°C)}} \times 100\,\%$$

Fig. 1. Normalized total power dissipation as a function of mounting base temperature



T_{mb} = 25 °C; I_{DM} is a single pulse

Fig. 2. Safe operating area; continuous and peak drain currents as a function of drain-source voltage



(1) $T_{j\ (init)}$ = 25 °C; (2) $T_{j\ (init)}$ = 150 °C; (3) Repetitive Avalanche

Fig. 3. Avalanche rating; avalanche current as a function of avalanche time

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$R_{th(j\text{-}mb)}$	thermal resistance from junction to mounting base	Fig. 4		-	0.29	0.38	K/W

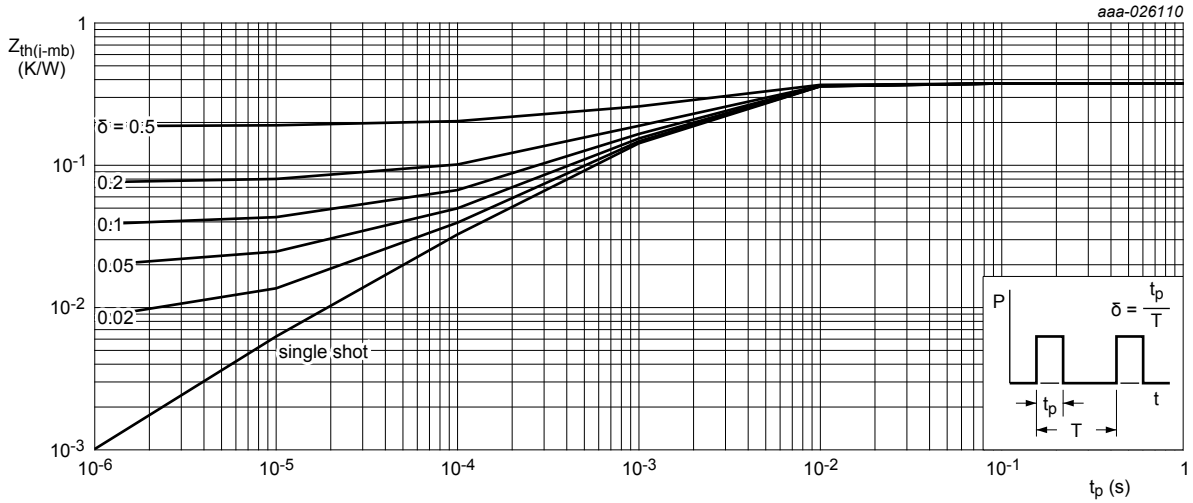


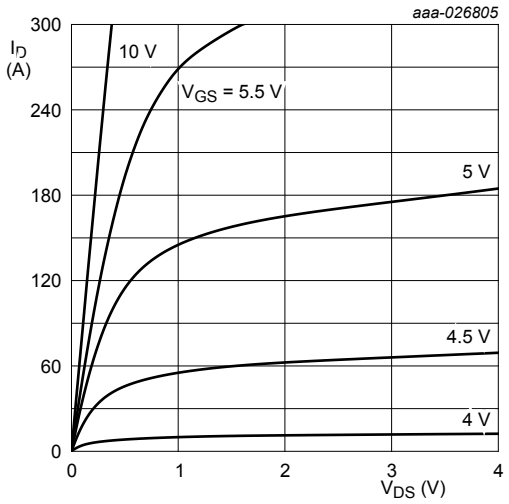
Fig. 4. Transient thermal impedance from junction to mounting base as a function of pulse duration

10. Characteristics

Table 7. Characteristics

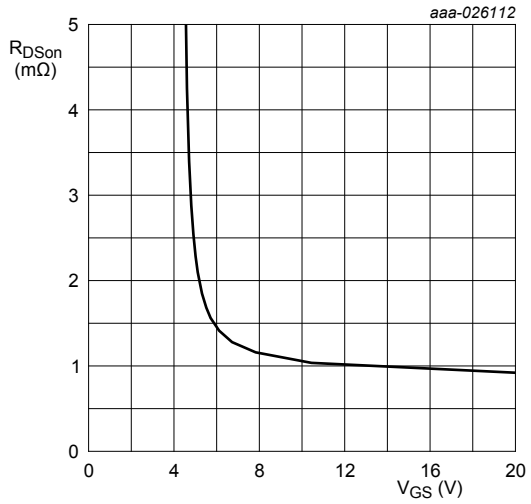
Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Static characteristics							
$V_{(BR)DSS}$	drain-source breakdown voltage	I_D = 250 µA; V_{GS} = 0 V; T_j = 25 °C		40	42	-	V
		I_D = 250 µA; V_{GS} = 0 V; T_j = -40 °C		-	39.6	-	V
		I_D = 250 µA; V_{GS} = 0 V; T_j = -55 °C		36	38.9	-	V
$V_{GS(th)}$	gate-source threshold voltage	I_D = 1 mA; V_{DS}=V_{GS}; T_j = 25 °C; Fig. 8; Fig. 9		2.4	3	3.6	V
		I_D = 1 mA; V_{DS}=V_{GS}; T_j = -55 °C; Fig. 8		-	-	4.3	V
		I_D = 1 mA; V_{DS}=V_{GS}; T_j = 175 °C; Fig. 8		1	-	-	V
I_{DSS}	drain leakage current	V_{DS} = 40 V; V_{GS} = 0 V; T_j = 25 °C		-	0.1	1	µA
		V_{DS} = 16 V; V_{GS} = 0 V; T_j = 125 °C		-	2.4	10	µA
		V_{DS} = 40 V; V_{GS} = 0 V; T_j = 175 °C		-	240	500	µA
I_{GSS}	gate leakage current	V_{GS} = 20 V; V_{DS} = 0 V; T_j = 25 °C		-	2	100	nA
		V_{GS} = -10 V; V_{DS} = 0 V; T_j = 25 °C		-	2	100	nA
R_{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I_D = 25 A; T_j = 25 °C; Fig. 10		0.74	1.06	1.4	mΩ
		V_{GS} = 10 V; I_D = 25 A; T_j = 105 °C; Fig. 11		1.05	1.57	2.23	mΩ
		V_{GS} = 10 V; I_D = 25 A; T_j = 125 °C; Fig. 11		1.16	1.74	2.45	mΩ
		V_{GS} = 10 V; I_D = 25 A; T_j = 175 °C; Fig. 11		1.46	2.18	3.05	mΩ
R_G	gate resistance	f = 1 MHz; T_j = 25 °C		0.4	1	2.5	Ω
Dynamic characteristics							
$Q_{G(tot)}$	total gate charge	I_D = 25 A; V_{DS} = 32 V; V_{GS} = 10 V; Fig. 12; Fig. 13		-	73	126	nC
Q_{GS}	gate-source charge			-	21	32	nC
Q_{GD}	gate-drain charge			-	13	34	nC
C_{iss}	input capacitance	V_{DS} = 25 V; V_{GS} = 0 V; f = 1 MHz; T_j = 25 °C; Fig. 14		-	5436	8155	pF
C_{oss}	output capacitance			-	1314	1840	pF
C_{rss}	reverse transfer capacitance			-	238	524	pF
$t_{d(on)}$	turn-on delay time	V_{DS} = 30 V; R_L = 1.2 Ω; V_{GS} = 10 V; $R_{G(ext)}$ = 5 Ω		-	19	-	ns
t_r	rise time			-	17	-	ns
$t_{d(off)}$	turn-off delay time			-	43	-	ns
t_f	fall time			-	21	-	ns
Source-drain diode							
V_{SD}	source-drain voltage	I_S = 25 A; V_{GS} = 0 V; T_j = 25 °C; Fig. 15		-	0.8	1.2	V

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
t_{rr}	reverse recovery time	I_S = 25 A; dI_S/dt = -100 A/µs; V_{GS} = 0 V; V_{DS} = 20 V		-	37	-	ns
Q_r	recovered charge			-	39	-	nC
S	softness factor	I_S = 25 A; dI_S/dt = -100 A/µs; V_{GS} = 0 V; V_{DS} = 20 V; T_j = 25 °C; Fig. 16		-	0.7	-	
		I_S = 25 A; dI_S/dt = -500 A/µs; V_{GS} = 0 V; V_{DS} = 20 V; T_j = 25 °C; Fig. 16		-	0.56	-	



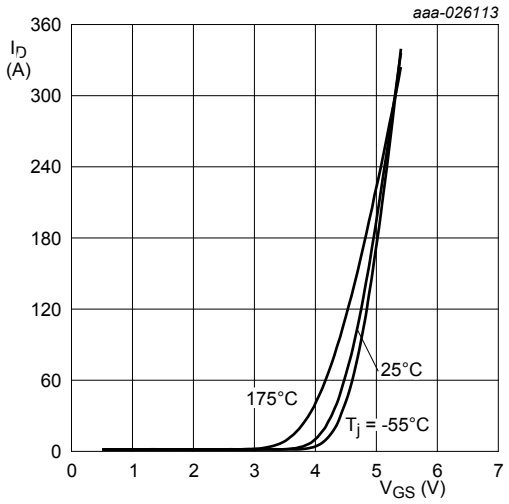
T_j = 25 °C

Fig. 5. Output characteristics; drain current as a function of drain-source voltage; typical values



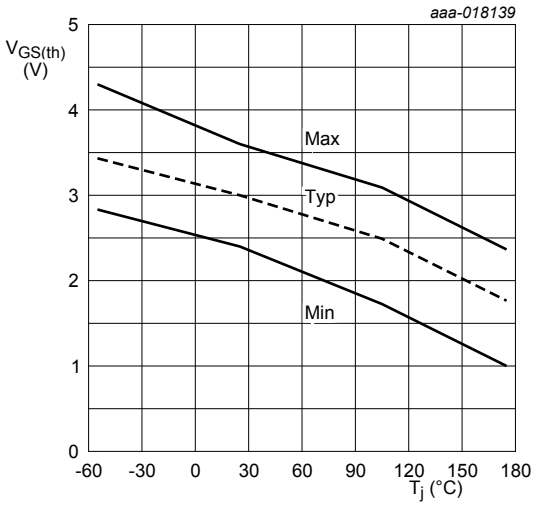
T_j = 25 °C; I_D = 25 A

Fig. 6. Drain-source on-state resistance as a function of gate-source voltage; typical values



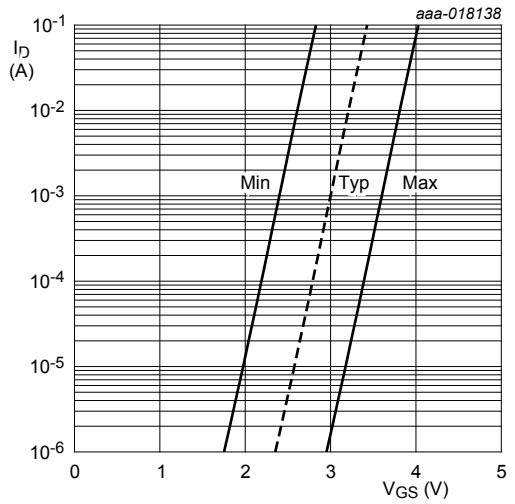
V_{DS} = 8 V

Fig. 7. Transfer characteristics; drain current as a function of gate-source voltage; typical values



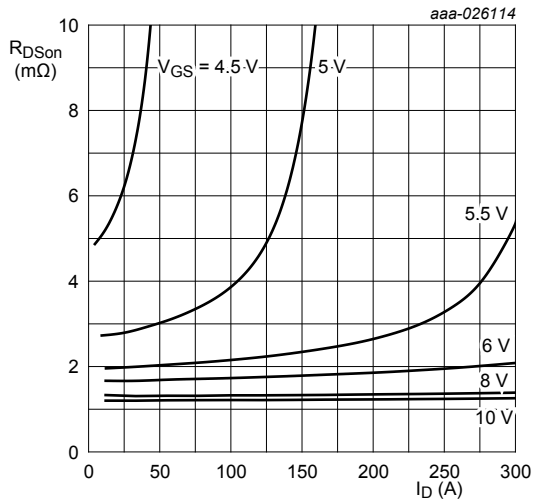
I_D = 1 mA ; V_{DS} = V_{GS}

Fig. 8. Gate-source threshold voltage as a function of junction temperature



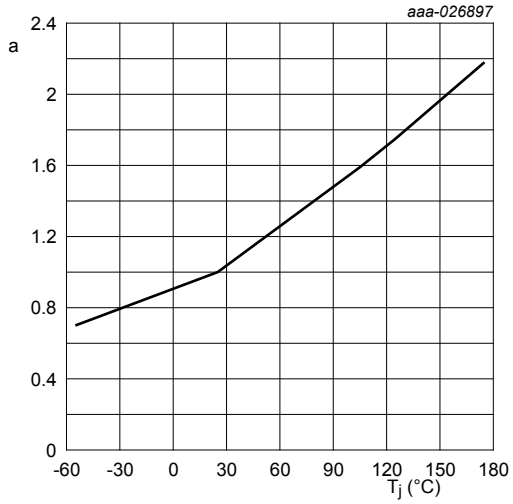
T_j = 25 °C; V_{DS} = 5V

Fig. 9. Sub-threshold drain current as a function of gate-source voltage



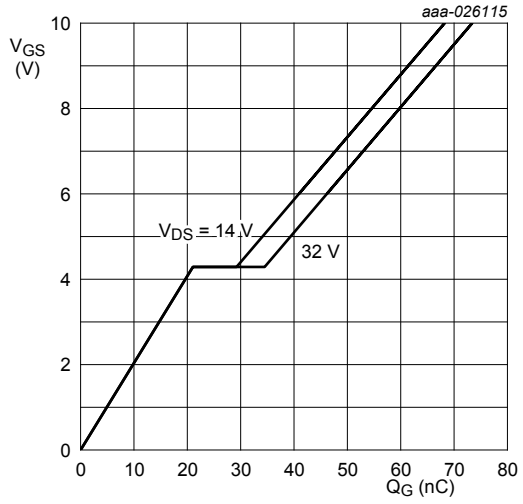
T_j = 25 °C

Fig. 10. Drain-source on-state resistance as a function of drain current; typical values



$$a = \frac{R_{DSon}}{R_{DSon\ (25°C)}}$$

Fig. 11. Normalized drain-source on-state resistance factor as a function of junction temperature



T_j = 25 °C; I_D = 25 A

Fig. 12. Gate-source voltage as a function of gate charge; typical values

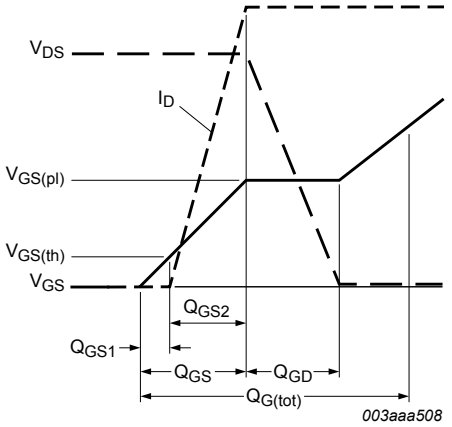
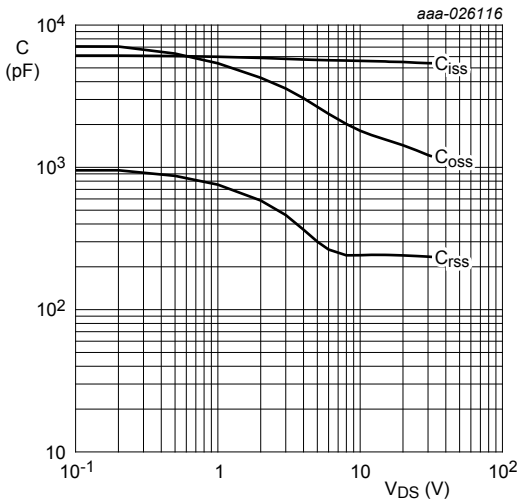
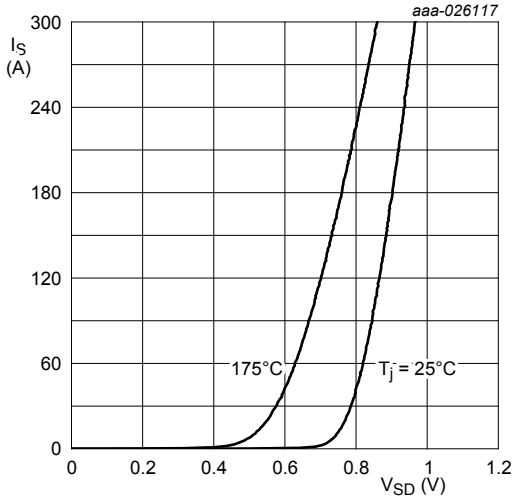


Fig. 13. Gate charge waveform definitions



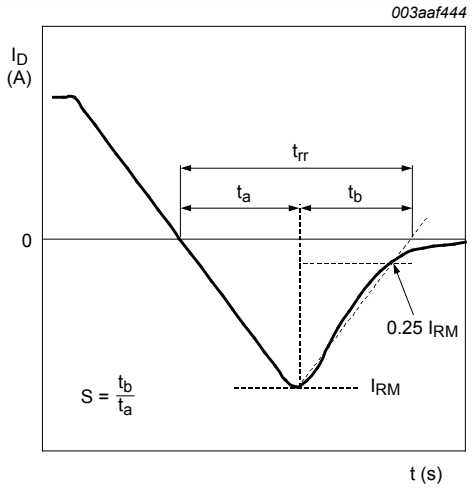
V_{GS} = 0 V; f = 1 MHz

Fig. 14. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values



V_{GS} = 0 V

Fig. 15. Source-drain (diode forward) current as a function of source-drain (diode forward) voltage; typical values

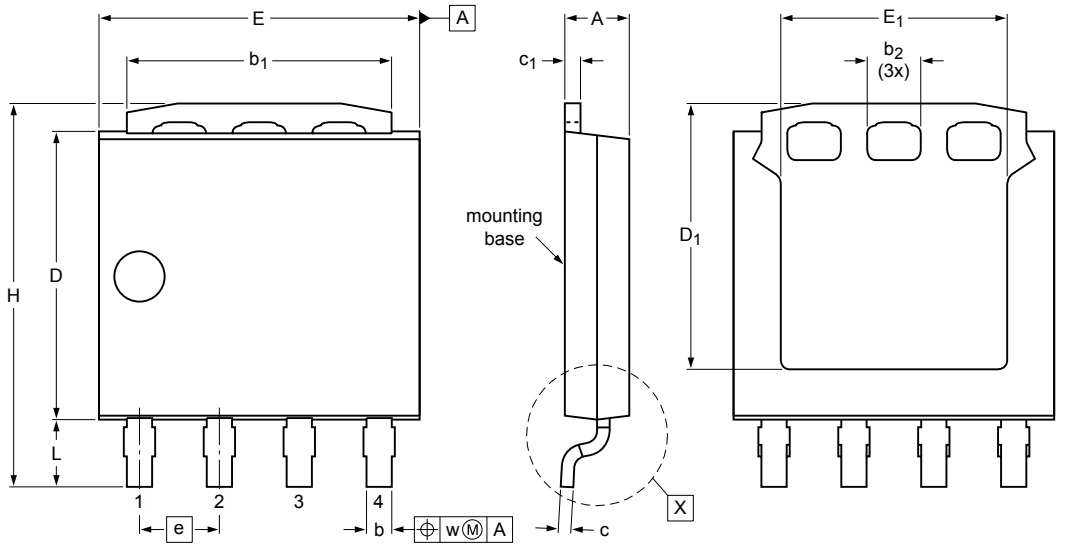


$t_{rr} = t_a + t_b$

Fig. 16. Reverse recovery waveform definitions

11. Package outline

Plastic single-ended surface-mounted package (LFPAK56E); 4 leads **SOT1023**



0 2.5 5 mm

scale

Dimensions

Unit		A	A_1	b	b_1	b_2	c	c_1	$D^{(1)}$	$D_1{}^{(1)}$	$E^{(1)}$	$E_1{}^{(1)}$	e	H	L	L_p	w	y	θ
mm	max	1.10	0.15	0.50	4.41		0.25	0.30	4.70	4.45	5.30	3.7		6.2	1.3	0.85			8°
	nom					0.85							1.27				0.25	0.1	
	min	0.95	0.00	0.35	3.62		0.19	0.24	4.45		4.95	3.5		5.9	0.8	0.40			0°

Note

1. Plastic or metal protrusions of 0.15 mm per side are not included.

sot1023_po

Outline version	References				European projection	Issue date
	IEC	JEDEC	JEITA			
SOT1023						~~13-03-05~~ 17-07-31

Fig. 17. Package outline LFPAK56E; Power-SO8 (SOT1023)

12. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.
[2] The term 'short data sheet' is explained in section "Definitions".
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13. Contents

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Date of release: 14 September 2017